

Magnetic properties of singlecrystalline $\text{Cd}_x\text{Mn}_y\text{Cr}_z\text{Se}_4$ ($0.03 \leq y \leq 0.12$)

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CdCr_2Se_4 spinel is a ferromagnetic semiconductor with the Curie temperature $T_C = 130$ K, Curie-Weiss temperature $\theta = 200$ K, saturation magnetization $M_S = 5.30 \mu_B/\text{f.u.}$ at 4.2 K and the effective magnetic moment $\mu_{\text{eff}} 5.49 = \mu_B/\text{f.u.}$ [1-3]. It has a structure of AB_2X_4 type with a lattice constant of 10.721-10.750 Å, in which the Se-anions form a cubic close-packed lattice, with the Cd-cations occupying the tetrahedral sites and the Cr-cations occupying the trigonal antiprismatic sites [2]. In CdCr_2Se_4 the magnetic order results from the competition of nearest neighbors positive Cr-Se-Cr interaction and more distant negative Cr-Se-Cd-Se-Cr exchange interaction [3]. Substitution of the manganese for the divalent cadmium ion showed the ferromagnetic order in polycrystalline $\text{Cd}_{0.85}\text{Mn}_{0.01}\text{Cr}_{1.97}\text{Se}_4$ spinel with the Curie temperature $T_C = 135$ K, Curie-Weiss temperature $\theta = 145$ K, saturation magnetization $M_S = 7.49 \mu_B/\text{f.u.}$ at 4.2 K and the effective magnetic moment $\mu_{\text{eff}} 5.76 = \mu_B/\text{f.u.}$ [4].

Magnetization measurements were carried out using a Quantum Design System (MPMS XL). Static (dc) magnetic susceptibility was measured in the magnetic field $H_{\text{dc}} = 100$ Oe and recorded in zero-field-cooled (ZFC) mode. Dynamic (ac) magnetic susceptibility was measured at an internal oscillating magnetic field $H_{\text{ac}} = 3.9$ Oe with an internal frequency $f = 300$ Hz. Both dc and ac magnetic susceptibility were measured in the temperature range 5–400 K. Magnetization isotherms were measured in the temperature range 5-275 K in static (dc) magnetic fields up to 70 kOe.

Magnetic measurements showed that the $\text{Cd}_x\text{Mn}_y\text{Cr}_z\text{Se}_4$ single crystals ($y = 0.03, 0.06, 0.09$ and 0.12) are ferromagnets with the Curie temperature $T_C = 130$ K, Curie-Weiss temperature $\theta = 161$ -183 K, saturation magnetization $M_S = 3.83$ -5.45 $\mu_B/\text{f.u.}$ at 5 K and the effective magnetic moment $\mu_{\text{eff}} 4.62$ -5.30 $= \mu_B/\text{f.u.}$, weakly dependent on the manganese substitution. The imaginary component of ac magnetic susceptibility showed strong energy loss in the long range of magnetic order, connected, for example, with the magnetic-domain-wall motion or with rotation of magnetization within domains [5]. The most interesting observation of magnetic measurements was magnetic hysteresis, which showed the existence of spontaneous magnetization and the coercive field in all crystals $\text{Cd}_x\text{Mn}_y\text{Cr}_z\text{Se}_4$, *i.e.* the typical ferromagnetic properties. Based on the experimentally set of magnetic hysteresis loops the values of spontaneous magnetization $M_S = 0.08 \mu_B/\text{f.u.}$ at 5 K and coercive field $H_C 19$ Oe were determined. The resulting hysteresis loops have a shape typical for affecting ferromagnetic material containing clusters of different sizes. Similar loops for $\text{Cd}_{1-x}\text{Mn}_x\text{GeAs}_2$ crystals were found [6].

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